Amendments to the Claims:

The following Listing of Claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Currently Amended) An article comprising:

a flexure assembly of a hard disk drive comprising a metal substrate and a dielectric film attached to said metal substrate, said dielectric film comprising a polymer selected from the group consisting of polyimides[, liquid crystal polymers,] and polycarbonates, wherein said dielectric film has been etched to a controlled thickness of less than about 20 μm from an original thickness of about 25 μm or greater.

2. (Original) An article according to claim 1 wherein the dielectric film is a polyimide having a carboxylic ester structural units in the polymer backbone.

3. (Original) An article according to claim 1 wherein the dielectric film is attached to the metal substrate by an adhesive layer.

4. (Cancelled)

5. (Original) An article according to claim 1 wherein the dielectric film has been etched to a thickness of less than about 10 μm.

6. (Original) An article according to claim 1 further comprising a patterned conductive layer on the dielectric layer.

7. (Original) An article according to claim 1 including at least one unsupported cantilevered lead.

8. (Withdrawn) A method comprising

providing a metal substrate,

attaching a dielectric film to said metal substrate, said dielectric film comprising a polymer selected from the group consisting of polyimides, liquid crystal polymers, and polycarbonates, said film having a thickness of about 25 μm or greater,

etching said dielectric film to a thickness of less than about 20 μm.

9. (Withdrawn) A method according to claim 8 wherein the dielectric film is a polyimide having a carboxylic ester structural unit in the polymer backbone.

10. (Withdrawn) A method according to claim 8 wherein the dielectric film is attached to the metal substrate by an adhesive layer.

11. (Withdrawn) A method according to claim 8 wherein the dielectric film is a liquid crystal polymer attached to the metal substrate without an adhesive layer.

12. (Withdrawn) A method according to claim 10 wherein the dielectric film has been etched to a thickness of less than about 10 μm.

13. (Withdrawn) A method according to claim 8 wherein the dielectric film is etched with an aqueous solution comprising

about 30wt.% to about 55wt.% of an alkali metal salt; and

about 10wt.% to about 35wt.% of a solubilizer dissolved in said solution.

14. (Withdrawn) A process according to claim 8 wherein said alkali metal salt is selected from the group consisting of sodium hydroxide and potassium hydroxide.

15. (Withdrawn) A process according to claim 8 wherein said solubilizer is an amine.

16. (Withdrawn) A process according to claim 8 wherein said solubilizer is ethanolamine.

17. (Withdrawn) A method according to claim 8 wherein the etching is carried out at a temperature of about 50°C to about 120°C.